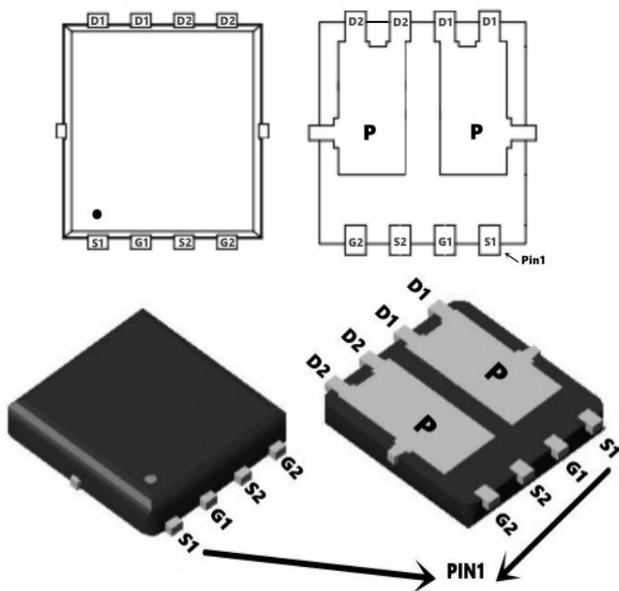


Description

The SX30V06NF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

$V_{DS} = -60V$ $I_D = -30A$

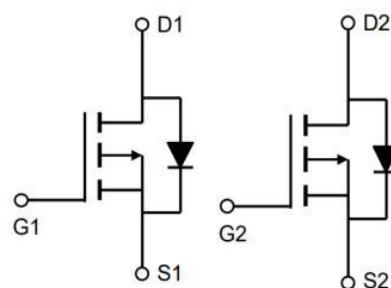
$R_{DS(ON)} < 35m\Omega$ @ $V_{GS} = -10V$

Application

Lithium battery protection

Wireless impact

Mobile phone fast charging



Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $-V_{GS} @ -10V^1$	-30	A
$I_D @ T_c = 100^\circ C$	Continuous Drain Current, $-V_{GS} @ -10V^1$	-27	A
I_{DM}	Pulsed Drain Current ²	-85	A
EAS	Single Pulse Avalanche Energy ³	113	mJ
IAS	Avalanche Current	47.6	A
$P_D @ T_c = 25^\circ C$	Total Power Dissipation ⁴	52.1	W
TSTG	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	25	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	2.4	°C/W

Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=-250\mu\text{A}$	-60	-68	---	V
$\Delta BVDSS/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.035	---	$\text{V}/^\circ\text{C}$
RDS(ON)	Static Drain-Source On-Resistance ²	$V_{GS}=-10\text{V}$, $I_D=-10\text{A}$	---	28	35	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$, $I_D=-8\text{A}$	---	33	38	
VGS(th)	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D = -250\mu\text{A}$	-1.0	-1.6	-2.5	V
$\Delta V_{GS(\text{th})}$	$V_{GS(\text{th})}$ Temperature Coefficient		---	4.28	---	$\text{mV}/^\circ\text{C}$
IDSS	Drain-Source Leakage Current	$V_{DS}=-48\text{V}$, $V_{GS}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	uA
		$V_{DS}=-48\text{V}$, $V_{GS}=0\text{V}$, $T_J=55^\circ\text{C}$	---	---	5	
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=-10\text{V}$, $I_D=-18\text{A}$	---	23	---	S
R _g	Gate Resistance	$V_{DS}=0\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	7	---	Ω
Q _g	Total Gate Charge (-4.5V)	$V_{DS}=-20\text{V}$, $V_{GS}=-4.5\text{V}$, $I_D=-12\text{A}$	---	25	---	nC
Q _{gs}	Gate-Source Charge		---	6.7	---	
Q _{gd}	Gate-Drain Charge		---	5.5	---	
Td(on)	Turn-On Delay Time	$V_{DD}=-15\text{V}$, $V_{GS}=-10\text{V}$, $R_G=3.3\Omega$, $I_D=-1\text{A}$	---	38	---	ns
T _r	Rise Time		---	23.6	---	
Td(off)	Turn-Off Delay Time		---	100	---	
T _f	Fall Time		---	6.8	---	
C _{iss}	Input Capacitance	$V_{DS}=-15\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	3635	---	pF
C _{oss}	Output Capacitance		---	224	---	
Crss	Reverse Transfer Capacitance		---	141	---	
I _s	Continuous Source Current ^{1,5}	$V_G=V_D=0\text{V}$, Force Current	---	---	-35	A
ISM	Pulsed Source Current ^{2,5}		---	---	-70	A
VSD	Diode Forward Voltage ²	$V_{GS}=0\text{V}$, $I_S=-1\text{A}$, $T_J=25^\circ\text{C}$	---	---	-1	V

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3、The EAS data shows Max. rating . The test condition is $VDD=-48\text{V}$, $VGS =-10\text{V}$, $L=0.1\text{mH}$, $IAS =-47.6\text{A}$
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

Typical Characteristics

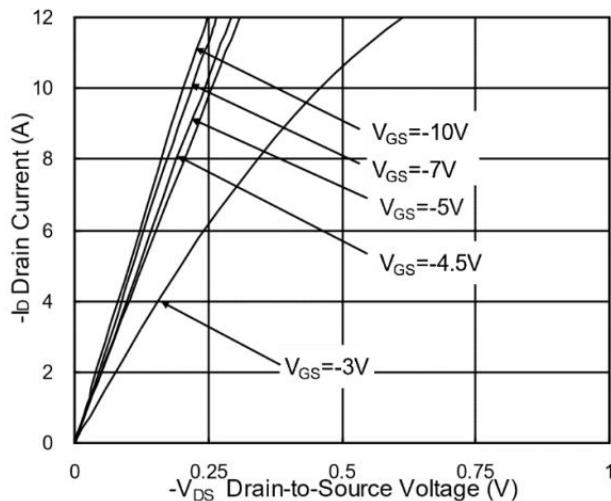


Fig.1 Typical Output Characteristics

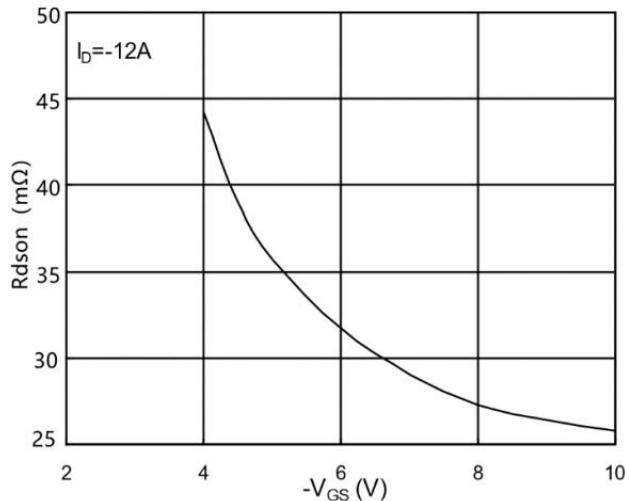


Fig.2 On-Resistance v.s Gate-Source

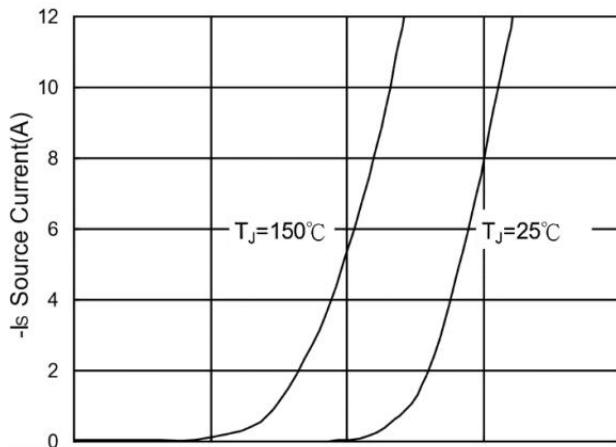


Fig.3 Forward Characteristics Of Reverse

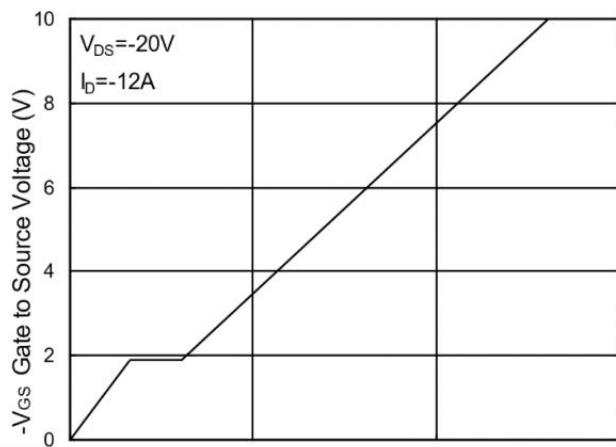


Fig.4 Gate-Charge Characteristics

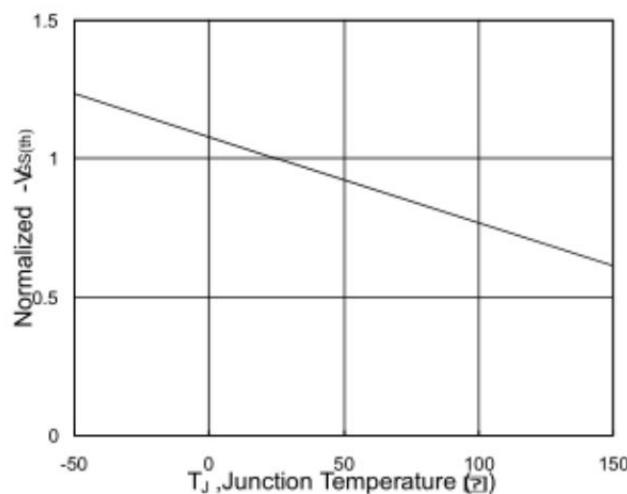


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

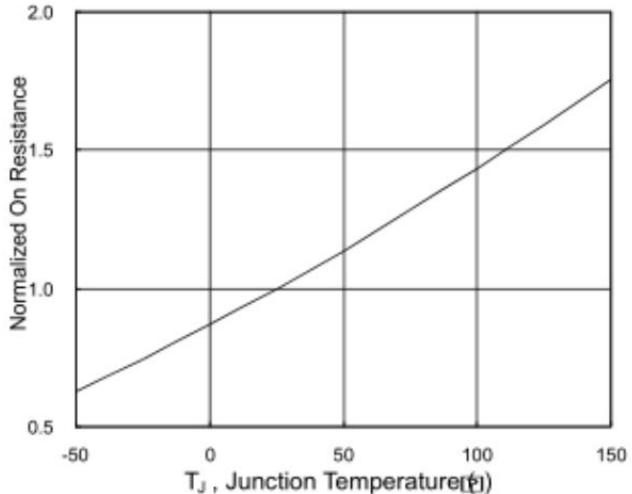


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

Typical Characteristics

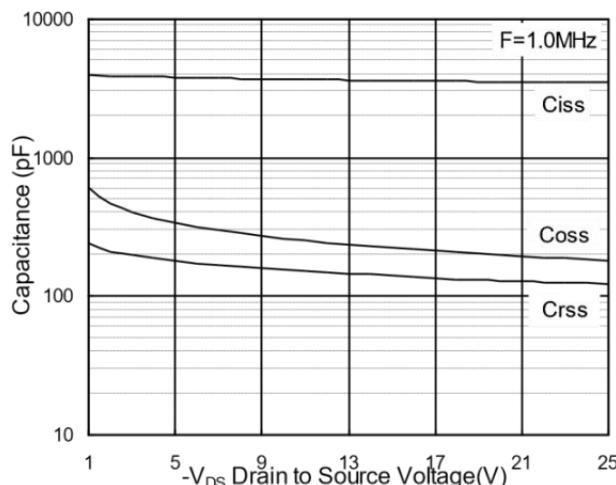


Fig.7 Capacitance

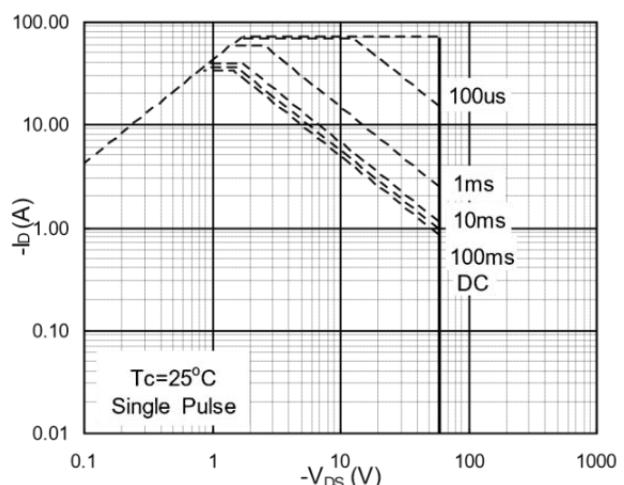


Fig.8 Safe Operating Area

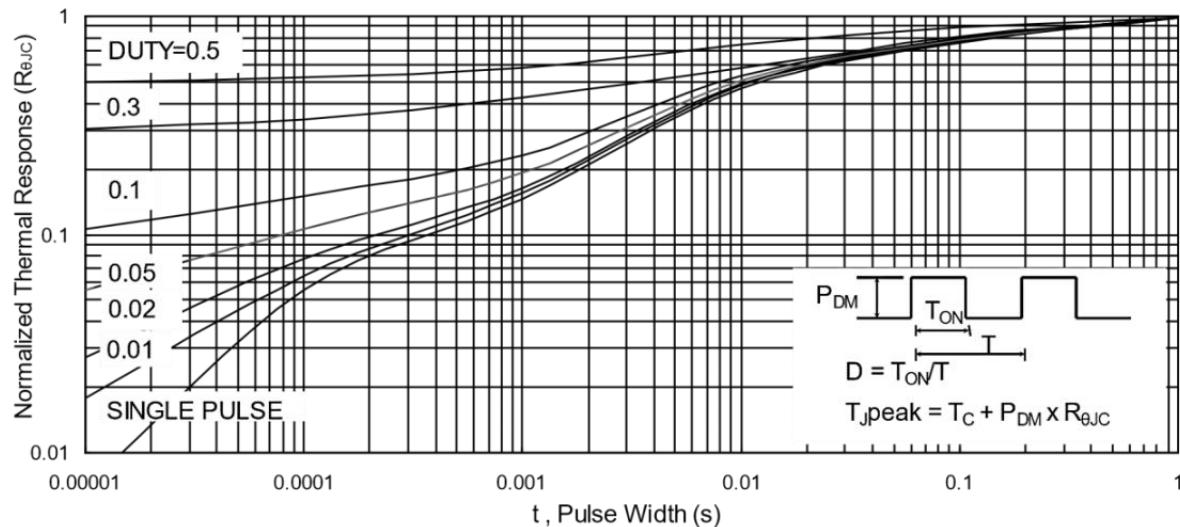


Fig.9 Normalized Maximum Transient Thermal Impedance

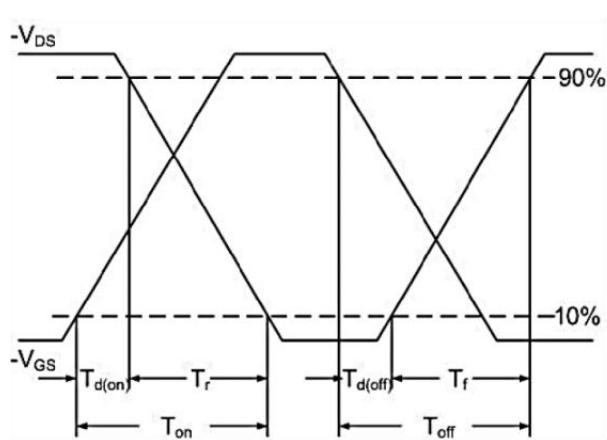


Fig.10 Switching Time Waveform

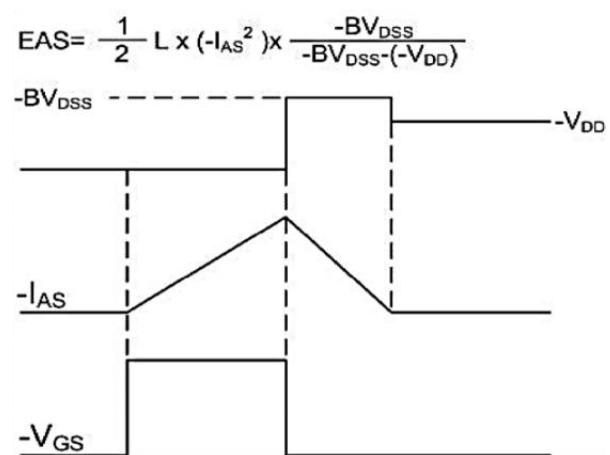
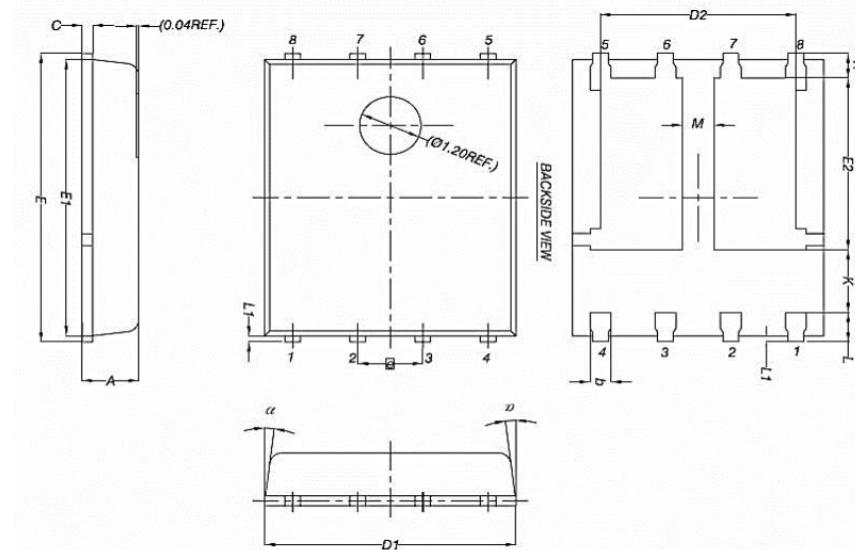


Fig.11 Unclamped Inductive Waveform

Package Mechanical Data-PDFN5*6-8L-JQ Double



Symbol	Common mm		
	Mim	Nom	Max
A	0.90	1.00	1.10
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	3.30	3.45
E2	3.38	3.05	3.20
e	1.27BSC		
H	0.41	0.51	0.61
K	1.10	--	--
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
M	0.50	--	--
a	0°	--	12°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN5*6-8L		5000